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## PATENT ABSTRACTS OF JAPAN

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(21) Application number: **06327512**(71) Applicant: **NEC CORP**(22) Date of filing: **28.12.94**(72) Inventor: **SAKURA NAOKI**(54) **MANUFACTURE OF SEMICONDUCTOR DEVICE**

pattern.

## (57) Abstract:

**PURPOSE:** To prevent pattern deformation due to contraction by heat treatment after development and prevent the adhesion of the pattern to the base substrate from deteriorating by forming a dummy pattern, which has resist left at the bottom, on a resist film at the time of exposing an hole opening pattern for element on the resist film.

**CONSTITUTION:** A positive photoresist is applied on a substrate 11 so as to form a resist film 12 (a), the resist film 12 is exposed by using a mask 13 and a resist pattern is provided by development (b). A dummy pattern is provided in the vicinity of the element pattern, approximately within  $5\mu\text{m}$ . The element pattern 14 is opened to the bottom by the design dimensions, the dummy pattern 15, however, is not developed to the bottom and the resist is left (c). The resist film 12 contracts after heat treatment, only the dummy pattern 15 is enlarged by the tensile stress of the resist, and a resist pattern without deformation is provided on the element pattern 14 in the outermost array of the element

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